

Please amend claims 3, 6 and 7 as follows:

Step 3. (Twice Amended) A method of making an n-type semiconductor diamond, characterized in that it comprises:

mechanically polishing a diamond substrate to make it in an inclined diamond substrate, which is formed by mechanically polishing a diamond (100) face oriented substrate so that its face normal is inclined at an angle between 1.5 and 6 degrees with respect to its <100> direction in a plane made by either its <100> and <010> directions or its <100> and <001> directions;

B2 subjecting a surface of said inclined diamond substrate to a smoothing treatment make it even:

exciting a raw material gas made of a volatile hydrocarbon compound, a sulfur compound and a hydrogen gas by a microwave plasma while maintaining at a given temperature said substrate surface smoothed as aforesaid to cause n-type semiconductor diamond to grow epitaxially on said smoothed substrate.

B3 6. (Twice Amended) A method of making an n-type semiconductor diamond as set forth in claim 3, characterized in that said smoothing treatment comprises a treatment of exposing said inclined substrate to the hydrogen plasma of a hydrogen pressure of 10 to 50 Torr and a microwave output of 200 to 1200 W at a substrate temperature of 700 to 1200 °C for a period of 0.5 hours to 5 hours, thereby to make even said substrate surface to consist of steps each in the order of an atomic layer.

Sub 1
03/20/01

7. (Twice Amended) A method of making an n-type semiconductor diamond as set forth in claim 3, characterized in that said given substrate temperature is between 700 and 1100°C.

[Please add new claim 20 as follows:]

By 20. A method of making an n-type semiconductor diamond as set forth in claim 7, characterized in that said given substrate temperature is 830°C.